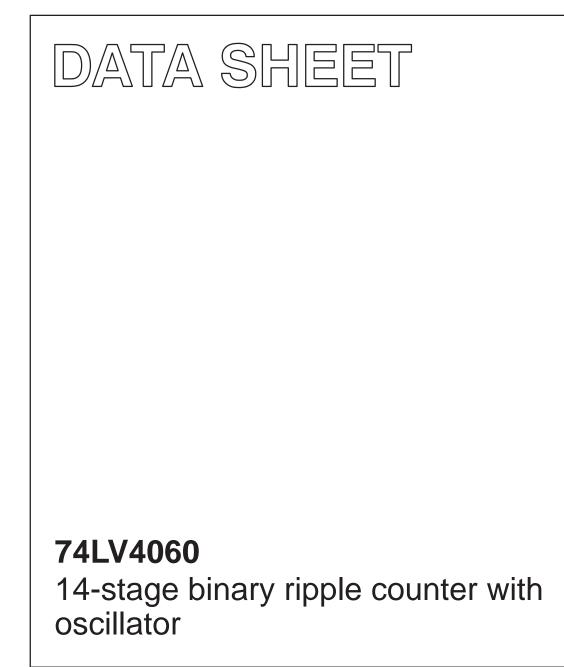
INTEGRATED CIRCUITS



Product specification

1998 Jun 23



74LV4060

FEATURES

- Wide operating voltage: 1.0 to 5.5 V
- Optimized for Low Voltage applications: 1.0 to 3.6 V
- Accepts TTL input levels between V_{CC} = 2.7 V and V_{CC} = 3.6 V
- Typical V_{OLP} (output ground bounce) < 0.8 V at V_{CC} = 3.3 V, $T_{amb} = 25$ °C.
- Typical V_{OHV} (output V_{OH} undershoot) > 2 V at V_{CC} = 3.3 V, T_{amb} = 25°C.
- All active components on chip
- RC or crystal oscillator configuration
- Output capability: standard (except for R_{TC} and C_{TC})
- I_{CC} category: MSI

APPLICATIONS

- Control Counters
- Timers
- Frequency Dividers
- Time-delay circuits

DESCRIPTION

The 74LV4060 is a low-voltage Si-gate CMOS device and is pin and function compatible with the 74HC/HCT4060.

The 74LV4060 is a 14-stage ripple-carry counter/divider and oscillator with three oscillator terminals (RS, R_{TC} and C_{TC}), ten buffered outputs (Q_3 to Q_9 and Q_{11} to Q_{13}) and an overriding asynchronous master reset (MR). The oscillator configuration allows design of either RC or crystal oscillator circuits. The oscillator may be replaced by an external clock signal at input RS. In this case, keep the oscillator pins (R_{TC} and C_{TC}) floating.

The counter advances on the negative-going transition of RS. A HIGH level on MR resets the counter (Q₃ to Q₉ and Q₁₁ to $Q_{13} = LOW$, independent of the other input conditions.

GND = 0 V; $T_{amb} = 25^{\circ}C$; $t_r = t_f \le 2.5 \text{ ns}$

SYMBOL	PARAMETER	CONDITIONS	TYPICAL	UNIT
	Propagation delay	C _L = 15 pF		
	RS to Q ₃	V _{CC} = 3.3 V	29	
t _{PHL} /t _{PLH}	Q _n to Q _{n+1}		6	ns
t _{PHL}	MR to Q _n		16	
f _{max}	Maximum clock frequency		99	MHz
C ₁	Input capacitance		3.5	pF
C _{PD}	Power dissipation capacitance per package	Notes 1, 2 and 3	40	pF

NOTES:

C_{PD} is used to determine the dynamic power 1.

dissipation (P_D in μW)

 $P_D = C_{PD} \times V_{CC}^2 \times f_i + \Sigma (C_L \times V_{CC}^2 \times f_o) \text{ where:}$ $f_i = \text{input frequency in MHz; } C_L = \text{output load capacity in pF;}$

fo = output frequency in MHz; V_{CC} = supply voltage in V;

 Σ (C_L x V_{CC}² x f_o) = sum of the outputs.

- 2. The condition is $V_1 = GND$ to V_{CC}
- 3. For formula on dynamic power dissipation, see the following pages.

ORDERING INFORMATION

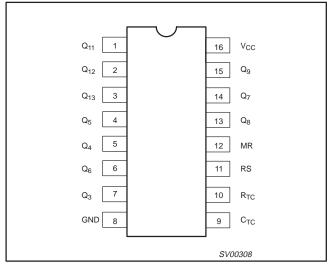
PACKAGES	TEMPERATURE RANGE	OUTSIDE NORTH AMERICA	NORTH AMERICA	PKG. DWG. #
16-Pin Plastic DIL	–40°C to +125°C	74LV4060 N	74LV4060 N	SOT38-4
16-Pin Plastic SO	–40°C to +125°C	74LV4060 D	74LV4060 D	SOT109-1
16-Pin Plastic SSOP Type II	–40°C to +125°C	74LV4060 DB	74LV4060 DB	SOT338-1
16-Pin Plastic TSSOP Type I	–40°C to +125°C	74LV4060 PW	74LV4060PW DH	SOT403-1

74LV4060

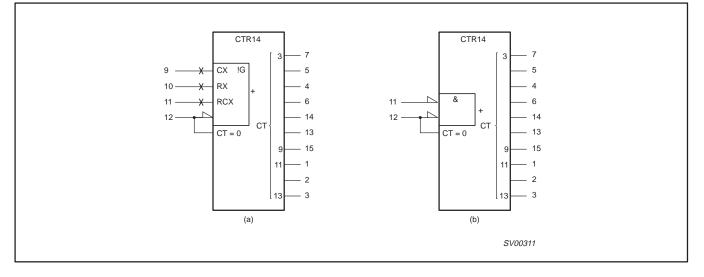
PIN DESCRIPTION

PIN NO.	SYMBOL	FUNCTION
1, 2, 3	Q ₁₁ to Q13	Counter outputs
7, 5, 4, 6, 15, 13, 15	Q_3 to Q_9	Counter outputs
8	GND	Ground (0 V)
9	C _{TC}	External capacitor connection
10	R _{TC}	External resistor connection
11	RS	Clock input/oscillator pin
12	MR	Master reset
16	V _{CC}	Positive supply voltage

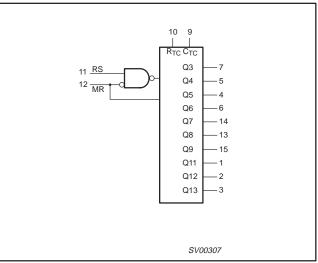
PIN CONFIGURATION



LOGIC SYMBOL (IEEE/IEC)



LOGIC SYMBOL



74LV4060

DYNAMIC POWER DISSIPATION

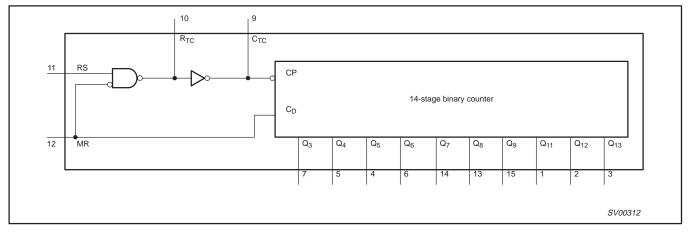
GND = 0 V; T_{amb} = 25 $^{\circ}$ C

PARAMETER	V _{CC} (V)	TYPICAL FORMULA FOR $P_D (\mu W)^1$
Total dynamic power dissipation when using the on–chip oscillator (P_D)	1.2 2.0 3.0	$ \begin{array}{l} C_{PD} x f_{osc} x V_{CC}{}^2 + \Sigma (C_L x V_{CC}{}^2 x f_o) + 2 C_t x V_{CC}{}^2 x f_{osc} + 16 x V_{CC} \\ C_{PD} x f_{osc} x V_{CC}{}^2 + \Sigma (C_L x V_{CC}{}^2 x f_o) + 2 C_t x V_{CC}{}^2 x f_{osc} + 460 x V_{CC} \\ C_{PD} x f_{osc} x V_{CC}{}^2 + \Sigma (C_L x V_{CC}{}^2 x f_o) + 2 C_t x V_{CC}{}^2 x f_{osc} + 1000 x V_{CC} \end{array} $

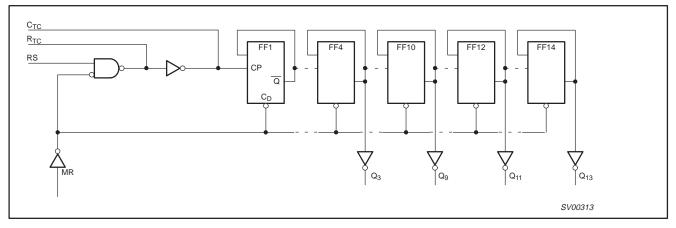
NOTE:

1. Where: $f_o = output$ frequency in MHz; $f_{osc} = oscillator$ frequency in MHz; $\Sigma (C_L \times V_{CC}^2 \times f_o) = sum of the outputs; C_L = output load capacitance in pF; C_t = timing capacitance in pF; V_{CC} = supply voltage in V.$

FUNCTIONAL DIAGRAM



LOGIC DIAGRAM



74LV4060

TIMING DIAGRAM 16 32 128 256 512 1.024 2.048 4.096 8.192 16.384 2 4 8 64 RS MR Q3 Q4 Q5 Q6 Q7 Q8 Q9 Q11 012 Q13 SV00309

ABSOLUTE MAXIMUM RATINGS^{1, 2}

In accordance with the Absolute Maximum Rating System (IEC 134) Voltages are referenced to GND (ground = 0V)

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V _{CC}	DC supply voltage		-0.5 to +7.0	V
±I _{IK}	DC input diode current	$V_{I} < -0.5 \text{ or } V_{I} > V_{CC} + 0.5 V$	20	mA
±I _{OK}	DC output diode current	$V_{\rm O}$ < -0.5 or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5V	50	mA
±IO	DC output source or sink current – standard outputs	$-0.5V < V_{O} < V_{CC} + 0.5V$	25	mA
±I _{GND} , ±I _{CC}	DC V _{CC} or GND current for types with –standard outputs		50	mA
T _{stg}	Storage temperature range		-65 to +150	°C
P _{TOT}	Power dissipation per package –plastic DIL –plastic mini-pack (SO) –plastic shrink mini-pack (SSOP and TSSOP)	for temperature range: -40 to +125°C above +70°C derate linearly with 12mW/K above +70°C derate linearly with 8 mW/K above +60°C derate linearly with 5.5 mW/K	750 500 400	mW

NOTES:

1. Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

2. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

74LV4060

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CC}	DC supply voltage	See Note ¹	1.0	3.3	5.5	V
VI	Input voltage		0	-	V _{CC}	V
Vo	Output voltage		0	-	V _{CC}	V
T _{amb}	Operating ambient temperature range in free air	See DC and AC characteristics	-40 -40		+85 +125	°C
t _r , t _f	Input rise and fall times	$\begin{array}{c} V_{CC} = 1.0V \text{ to } 2.0V \\ V_{CC} = 2.0V \text{ to } 2.7V \\ V_{CC} = 2.7V \text{ to } 3.6V \\ V_{CC} = 3.6V \text{ to } 5.5V \end{array}$	- - -	- - -	500 200 100 50	ns/V

NOTES:

1. The LV is guaranteed to function down to V_{CC} = 1.0V (input levels GND or V_{CC}); DC characteristics are guaranteed from V_{CC} = 1.2V to V_{CC} = 5.5V.

DC CHARACTERISTICS

Over operating conditions, voltages are referenced to GND (ground = 0 V)

					LIMITS				
SYMBOL	PARAMETER	TEST CONDITIONS	-40	°C to +8	5°C	-40°C to	o +125°C	UNIT	
			MIN	TYP ¹	MAX	MIN	MAX	1	
		$V_{CC} = 1.2V$	0.9	-	-	0.9	-		
VIH	HIGH level Input	$V_{CC} = 2.0V$	1.4	-	- 1	1.4	-	V	
VIH	voltage MR input	V _{CC} = 2.7 to 3.6V	2.0	-	-	2.0	-	ľ	
		V _{CC} = 4.5 to 5.5V	0.7 * V _{CC}	-	-	0.7 * V _{CC}	-	1	
		$V_{CC} = 1.2V$	-	-	0.3	-	0.3		
V	LOW level Input	$V_{CC} = 2.0 V$	-	-	0.6	-	0.6	V	
VIL	voltage MR input	V _{CC} = 2.7 to 3.6V	-	-	0.8	-	0.8	ľ	
		V _{CC} = 4.5 to 5.5	-	-	0.3 * V _{CC}	-	0.3 * V _{CC}	1	
		$V_{CC} = 1.2V$	1.0	-	-	1.0	-		
V	HIGH level Input	$V_{CC} = 2.0 V$	1.6	-	-	1.6	-	V	
VIH	voltage RS input	V _{CC} = 2.7 to 3.6V	2.4	-	-	2.4	-		
		V _{CC} = 4.5 to 5.5V	0.8 * V _{CC}	-	-	0.8 * V _{CC}	-	1	
		$V_{CC} = 1.2V$	-	-	0.2	-	0.2		
VII	LOW level Input voltage	$V_{CC} = 2.0 V$	-	-	0.4	-	0.4	v	
V IL	RS input	V _{CC} = 2.7 to 3.6V	-	-	0.5	-	0.5	ľ	
		V _{CC} = 4.5 to 5.5	-	-	0.2 * V _{CC}	-	0.2 * V _{CC}	1	
		V_{CC} = 1.2V; RS = GND and MR = GND; -I _O = 3.4mA	-	-	-	-	-		
		V_{CC} = 2.0V; RS = GND and MR = GND; -I _O = 3.4mA	-	_	-	-	-		
V _{OH}	HIGH level output voltage; R _{TC} output	V_{CC} = 2.7V; RS = GND and MR = GND; -I _O = 3.4mA	-	-	-	-	-	V	
		V_{CC} = 3.0V; RS = GND and MR = GND; $-I_O$ = 3.4mA	2.40	2.82	-	2.20	-		
		V_{CC} = 4.5V; RS = GND and MR = GND; -I _O = 3.4mA	-	-	-	-	-	1	

Philips Semiconductors

14-stage binary ripple counter with oscillator

				LIMITS					
SYMBOL	PARAMETER		-4	0°C to +85	5°C	-40°C to	o +125°C		
		V_{CC} = 1.2V; RS = V_{CC} and MR = V_{CC} ; -I _O = 0.8mA	-	-	-	-	-		
		V_{CC} = 2.0V; RS = V_{CC} and MR = V_{CC} ; -I _O = 0.8mA	-	-	_	-	-		
V _{OH}	HIGH level output voltage;	V_{CC} = 2.7V; RS = V_{CC} and MR = V_{CC} ; -I _O = 0.8mA	-	-	_	-	-	V	
	R _{TC} output	V_{CC} = 3.0V; RS = V_{CC} and MR = V_{CC} ; -I _O = 0.8mA	2.40	2.82	_	2.20	-	1	
		V_{CC} = 4.5V; RS = V_{CC} and MR = $V_{CC;}$ –I_O = 0.8mA	-	-	-	-	-	1	
		V_{CC} = 1.2V; RS = GND and MR = GND; -I _O = 100µA	1.0	1.2	-	1.0	-		
		V_{CC} = 2.0V; RS = GND and MR = GND; -I _O = 100µA	1.8	2.0	-	1.8	-	1	
V _{OH}	HIGH level output voltage; R _{TC} output	V_{CC} = 2.7V; RS = GND and MR = GND; -I _O = 100µA	-	-	-	-	-	V	
		V_{CC} = 3.0V; RS = GND and MR = GND; $-I_O$ = 100 μA	2.8	3.0	_	2.8	-	1	
		V_{CC} = 4.5V; RS = GND and MR = GND; $-I_O$ = 100 μA	-	-	-	-	-	1	
	HIGH level output voltage; R _{TC} output	V_{CC} = 1.2V; RS = V_{CC} and MR = $V_{CC;}$ –I_0 = 100 μA	1.0	1.2	-	1.0	-		
		V_{CC} = 2.0V; RS = V_{CC} and MR = $V_{CC;}$ –I_0 = 100 μA	1.8	2.0	_	1.8	-	1	
V _{OH}		V_{CC} = 2.7V; RS = V_{CC} and MR = $V_{CC;}$ $-I_O$ = 100 μA	-	-	-	-	-	V	
		V_{CC} = 3.0V; RS = V_{CC} and MR = $V_{CC;}$ $-I_O$ = 100 μA	2.8	3.0	-	2.8	-		
		V_{CC} = 4.5V; RS = V_{CC} and MR = $V_{CC;}$ $-I_O$ = 100 μA	-	-	-	-	-]	
		V_{CC} = 1.2V; RS = V_{IH} and MR = $V_{IL;}$ $-I_O$ = 3.8mA		1.2	_	-	_		
		V_{CC} = 2.0V; RS = V_{IH} and MR = $V_{IL;}$ $-I_O$ = 3.8mA	-	-	-	-	-]	
V _{OH}	HIGH level output voltage; C _{TC} output	V_{CC} = 2.7V; RS = V_{IH} and MR = $V_{IL;}$ $-I_O$ = 3.8mA	-	-	-	-	-	V	
		V_{CC} = 3.0V; RS = V_{IH} and MR = $V_{IL;}$ $-I_O$ = 3.8mA	2.40	2.82	_	2.20	-		
		V_{CC} = 4.5V; RS = V_{IH} and MR = $V_{IL;}$ $-I_O$ = 3.8mA	-	-	-	-	-		
		V_{CC} = 1.2V; V_I = V_{IH} and V_I = $V_{IL;}$ $-I_O$ = 100 μA	1.0	1.2	_	1.0	-		
		V_{CC} = 2.0V; V_I = V_{IH} and V_I = $V_{IL;}$ $-I_O$ = 100 μA	1.8	2.0	_	1.8	-		
V _{OH}	HIGH level output voltage; except R _{TC} output	V_{CC} = 2.7V; V_I = V_{IH} and V_I = $V_{IL;}$ $-I_O$ = 100 μA	-	-	-	-	-	V	
		V_{CC} = 3.0V; V_{I} = V_{IH} and V_{I} = $V_{IL;}$ $-I_{O}$ = 100 μA	2.8	3.0	_	2.8	-		
		V_{CC} = 4.5V; V_I = V_{IH} and V_I = $V_{IL;}$ $-I_O$ = 100 μA	-	-	-	-	-	1	

Philips Semiconductors

14-stage binary ripple counter with oscillator

			LIMITS					
SYMBOL	PARAMETER	TEST CONDITIONS	-40°C to +85°C			-40°C to	o +125°C	
		$V_{CC} = 1.2V$; $V_I = V_{IH}$ and $V_I = V_{IL}$; $-I_O = 6mA$	-	-	-	-	-	
	HIGH level output	$V_{CC} = 2.0V$; $V_I = V_{IH}$ and $V_I = V_{IL}$; $-I_O = 6mA$	-	-	-	-	-	1
Maria	voltage; except R _{TC} and	$V_{CC} = 2.7V$; $V_I = V_{IH}$ and $V_I = V_{IL}$; $-I_O = 6mA$	-	-	-	-	-	V
	C _{TC} outputs	$V_{CC} = 3.0V$; $V_I = V_{IH}$ and $V_I = V_{IL}$; $-I_O = 6mA$	2.40	2.82	-	2.20	-	1
		$V_{CC} = 4.5$ V; $V_I = V_{IH}$ and $V_I = V_{IL}$; $-I_O = 6$ mA	-	-	_	-	-	1
		V_{CC} = 1.2V; RS = V_{CC} and MR = GND; -I _O = 3.4mA	-	-	_	-	-	
		V_{CC} = 2.0V; RS = V_{CC} and MR = GND; -I _O = 3.4mA	-	-	_	-	-	V
V _{OL}	LOW level output voltage; R _{TC} output	V_{CC} = 2.7V; RS = V_{CC} and MR = GND; $-I_O$ = 3.4mA	-	-	_	-	-	1
	KIC output	V_{CC} = 3.0V; RS = V_{CC} and MR = GND; $-I_O$ = 3.4mA	-	0.25	0.40	-	0.50	V
		V_{CC} = 4.5V; RS = V_{CC} and MR = GND; $-I_O$ = 3.4mA	-	-	-	-	-	V
		V_{CC} = 1.2V; RS = V_{CC} and MR = GND; $-I_O$ = 100 μA	-	0	0.2	-	0.2	
	LOW level output voltage; R _{TC} output	V_{CC} = 2.0V; RS = V_{CC} and MR = GND; $-I_{O}$ = 100 μA	-	0	0.2	-	0.2	1
V _{OL}		V_{CC} = 2.7V; RS = V_{CC} and MR = GND; $-I_O$ = 100 μA	-	-	_	-	-	V
	KIC ouput	V_{CC} = 3.0V; RS = V_{CC} and MR = GND; $-I_O$ = 100 μA	-	0	0.2	-	0.2	1
		V_{CC} = 4.5V; RS = V_{CC} and MR = GND; $-I_O$ = 100 μA	-	-	_	-	-	1
		V_{CC} = 1.2V; RS = V_{IH} and MR = $V_{IL;}$ $-I_O$ = 3.8mA	-	-	-	-	-	
		V_{CC} = 2.0V; RS = V_{IH} and MR = $V_{IL;}$ $-I_O$ = 3.8mA	-	-	-	-	-]
V _{OL}	LOW level output voltage; C _{TC} output	V_{CC} = 2.7V; RS = V_{IH} and MR = $V_{IL;}$ $-I_O$ = 3.8mA	-	-	-	-	-	V
		V_{CC} = 3.0V; RS = V_{IH} and MR = $V_{IL;}$ $-I_O$ = 3.8mA	-	0.25	0.40	-	0.50]
		V_{CC} = 4.5V; RS = V_{IH} and MR = $V_{IL;}$ $-I_O$ = 3.8mA	-	-	-	-	-]
		V_{CC} = 1.2V; V_I = V_{IH} and V_I = $V_{IL;}$ $-I_O$ = 100 μA	-	0	0.2	-	0.2	
		V_{CC} = 2.0V; V_I = V_{IH} and V_I = $V_{IL;}$ $-I_O$ = 100 μA	-	0	0.2	-	0.2]
V _{OL}	LOW level output voltage; except R _{TC} output	V_{CC} = 2.7V; V_{I} = V_{IH} and V_{I} = $V_{IL;}$ $-I_{O}$ = 100 μA	-	-	_	-	_	V
		V_{CC} = 3.0V; V_{I} = V_{IH} and V_{I} = $V_{IL;}$ $-I_{O}$ = 100 μA	-	0	0.2	-	0.2]
		V_{CC} = 4.5V; V_I = V_{IH} and V_I = $V_{IL;}$ $-I_O$ = 100 μA	-	-	_	-	-]

74LV4060

			LIMITS						
SYMBOL	PARAMETER	TEST CONDITIONS	ONS -40°C to +85°C			-40°C to	o +125°C		
		V_{CC} = 1.2V; V_{I} = V_{IH} and V_{I} = $V_{IL;}$ –I_O = 6mA	-	-	-	-	-		
	HIGH level output	V_{CC} = 2.0V; V_{I} = V_{IH} and V_{I} = $V_{IL;}$ $-I_{O}$ = 6mA	-	-	-	-	-]	
V _{OL} voltage; except R _{TC} and	V_{CC} = 2.7V; V_{I} = V_{IH} and V_{I} = $V_{IL;}$ $-I_{O}$ = 6mA	-	0.25	0.40	-	0.50	V		
	C _{TC} outputs	V_{CC} = 3.0V; V_{I} = V_{IH} and V_{I} = $V_{IL;}$ $-I_{O}$ = 6mA	-	-	-	-	-]	
		V_{CC} = 4.5V; V_{I} = V_{IH} and V_{I} = $V_{IL;}$ $-I_{O}$ = 6mA	-	-	-	-	-		
l	Input leakage current	$V_{CC} = 5.5V; V_I = V_{CC} \text{ or GND}$	-	-	1.0	-	1.0	μΑ	
las	Quiescent supply current	$V_{CC} = 3.6V; V_I = V_{CC} \text{ or GND}; I_O = 0$	-	-	20	-	160	μA	
Icc	Quiescent supply current	$V_{CC} = 5.5V; V_I = V_{CC} \text{ or GND}; I_O = 0$	-	-	-	-	80]	
ΔI _{CC}	Additional quiescent supply current per input pin	$V_{CC} = 2.7V$ to 3.6V; $V_{I} = V_{CC} - 0.6V$; $I_{O} = 0$	_	-	500	_	850	μA	

NOTE:

1. All typical values are measured at $T_{amb} = 25^{\circ}C$.

AC CHARACTERISTICS

GND = 0V; $t_r = t_f = 2.5ns$; $C_L = 50pF$; $R_L = 500\Omega$

SYMBOL	PARAMETER	WAVEFORM	CONDITION	_	LIMITS 40 to +85	°C		IITS +125 ℃	UNIT	
			V _{CC} (V)	MIN	TYP ¹	MAX	MIN	MAX		
			1.2	-	180	-	-	-		
	Developed to a state of	[2.0	-	52	84	-	105		
t _{PHL} /t _{PLH}	Propagation delay RS to Q ₃	Figures, 6, 8	2.7	-	42	66	-	83	ns	
		[3.0 to 3.6	-	33 ²	53	-	66		
		[4.5 to 5.5	-	24	39	-	49		
			1.2	-	40	-	-	-		
		[2.0	-	14	23	-	29		
t _{PHL} /t _{PLH}	Propagation delay Q _n to Q _{n+1}	Figures 7, 8	2.7	-	10	16	-	20	ns	
		1	3.0 to 3.6	-	8 ²	13	-	16		
		1	4.5 to 5.5	-	6	9	-	11		
			1.2	-	100	-	-	-		
		D <i>i</i> i i		1	2.0	-	29	46	-	58
t _{PHL}	Propagation delay MR to Q _n	Figures 7, 8	2.7	-	24	39	-	49	ns	
	Mire to den	1 1	3.0 to 3.6	-	19 ²	31	-	39		
		1 1	4.5 to 5.5	-	14	23	-	29		
			2.0	34	9	-	38	-		
*	Clock pulse width	Figure 6	2.7	25	6	-	30	-	ns	
t _W	RS; HIGH or LOW	Figure 6	3.0 to 3.6	20	5	-	24	-	115	
		1	4.5 to 5.5	16	4	-	20	-		
			2.0	34	10	-	38	-		
t	Master reset pulse	Figure 7	2.7	25	8	-	30	-	00	
tw	width MR; HIGH	Figure /	3.0 to 3.6	20	6	-	24	-	ns	
		1	4.5 to 5.5	16	4	-	20	-		

Philips Semiconductors

14-stage binary ripple counter with oscillator

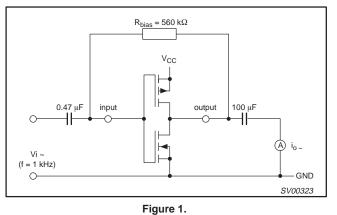
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SYMBOL	PARAMETER	WAVEFORM	CONDITION	_	LIMITS -40 to +85 °C			LIMITS -40 to +125 °C	
			V _{CC} (V)	MIN	TYP ¹	MAX	MIN	MAX	1
t _{rem}	Removal time MR to RS		2.0	29	18	-	37	-	ns
		Eiguro 7	2.7	26	16	-	32	-	
		Figure 7	3.0 to 3.6	18	11	-	23	-	
			4.5 to 5.5	12	7	-	15	-	
f _{max}	Maximum clock pulse frequency	Figure 6	2.0	14	40	-	9	-	MHz
			2.7	19	70	-	12	-	
			3.0 to 3.6	24	90	-	15	-	
			4.5 to 5.5	30	100	-	19	-	

NOTE:

Unless otherwise stated, all typical values are at $T_{amb} = 25^{\circ}C$. 1. Typical value measured at $V_{CC} = 3.3V$.

- 2. Typical value measured at $V_{CC} = 5.0V$.



Test set-up for measuring forward transconductance $g_{fs} = di_0/dv_i$ at v_0 is constant (see also graph Figure 2); MR = LOW.

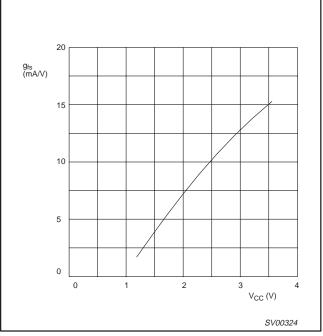
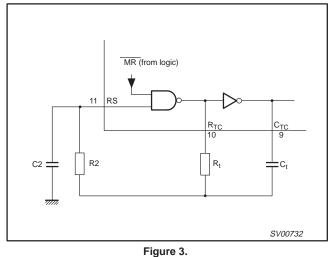
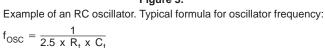


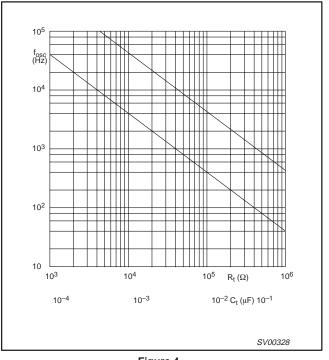
Figure 2.

Typical forward transconductance $\ensuremath{\mathsf{g}_{\mathsf{fs}}}$ as a function of the supply voltage V_{CC} at $T_{amb} = 25$ °C.

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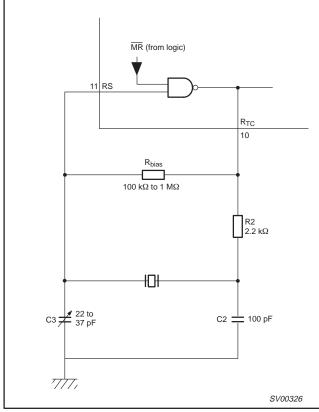


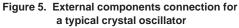
 $\label{eq:constraint} \begin{array}{l} \mbox{Figure 4.} \\ \mbox{RC oscillator frequency as a function of R_t and C_t at V_{CC} = 1.2 to 3.6 V; T_{amb} = 25 °C. C_t curve at R_t = 100 k\Omega; $R2$ = 200 k\Omega. R_t curve at C_t = 1 nF; $R2$ = 2 x R_t. } \end{array}$

TIMING COMPONENTS LIMITATIONS

The oscillator frequency is mainly determined by $R_t \cdot C_t$, provided $R_2 \approx 2R_t$ and $R_2 \cdot C_2 \ll R_t \cdot C_t$. The function of R2 is to minimize the influence of the forward voltage across the input protection diodes on the frequency. The stray capacitance C2 should be kept as small as possible. In consideration of accuracy, C_t must be larger than the inherent stray capacitance. R_t must be larger than the 'ON' resistance in series with it, which typically is 280 Ω at $V_{CC} = 1.2$ V, 130 Ω at $V_{CC} = 2.0$ V and 100 Ω at $V_{CC} = 3.0$ V. The recommended values for these components to maintain agreement with the typical oscillation formula are: $C_t > 50$ pF, up to any practical value, 10 k $\Omega < R_t < 1$ M Ω . In order to avoid start-up problems, $R_t \ge 1$ k Ω .

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R2 is the power limiting resistor. For starting and maintaining oscillation, a minimum transconductance is necessary, so R2 should not be too large. A practical value for R2 is 2.2 k Ω .

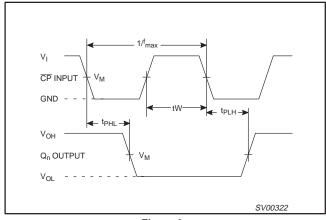


Figure 6.

Waveforms showing the clock (RS) to output (Q₃) propagation delays, the clock pulse width, the output transition times and the maximum clock frequency.

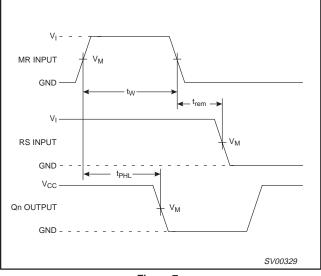


Figure 7.

Waveforms showing the master reset (MR) pulse width, the master reset to output (Qn) propagation delays and the master reset to clock (RS) removal time.

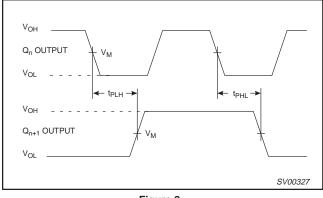


Figure 8.

Waveforms showing the output Q_n to output n + 1 propagation delays.

NOTES:

- V_M = 1.5 V at V_{CC} ≥ 2.7 V and ≤ 3.6 V V_M = 0.5 · V_{CC} at V_{CC} < 2.7 V and ≥ 4.5 V.
 V_{OL} and V_{OH} are the typical output voltage drop that occur with the output load.

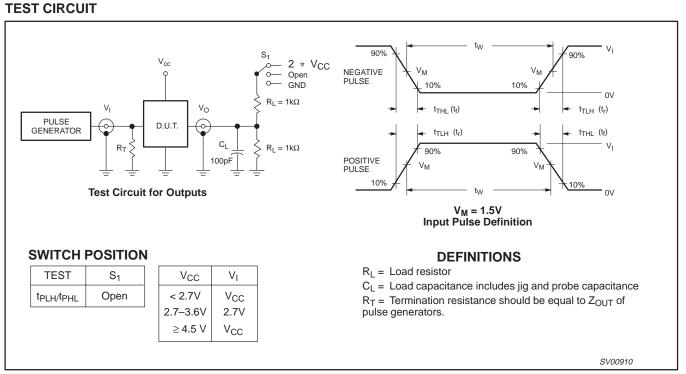
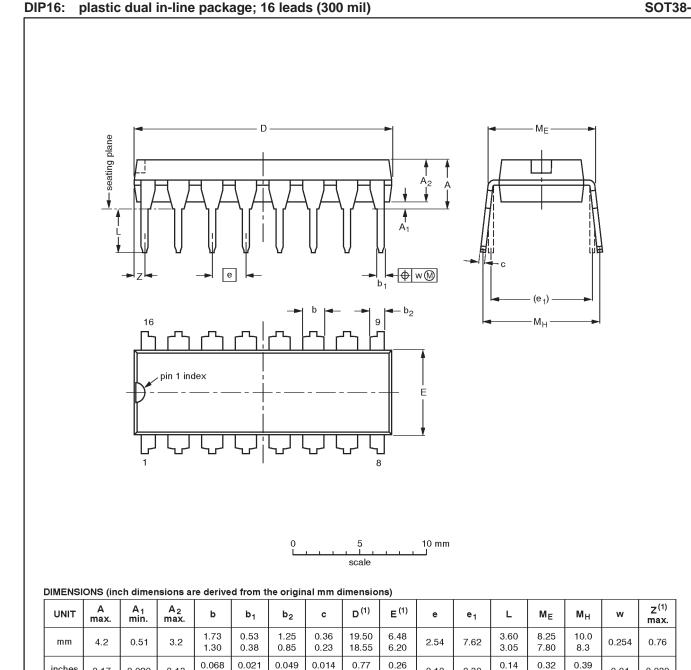


Figure 9. Load circuitry for switching times.



inches

0.17

0.020

0.13

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

0.051

0.015

0.033

0.009

OUTLINE	REFERENCES				EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE	
SOT38-4						-92-11-17 95-01-14	

0.73

0.24

0.10

0.30

0.12

0.31

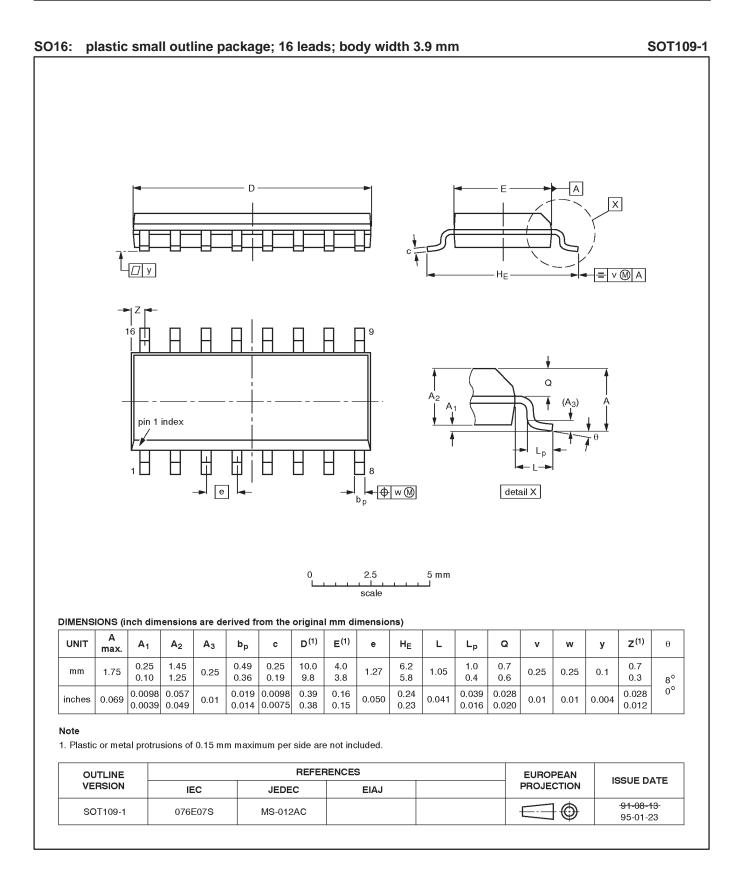
0.33

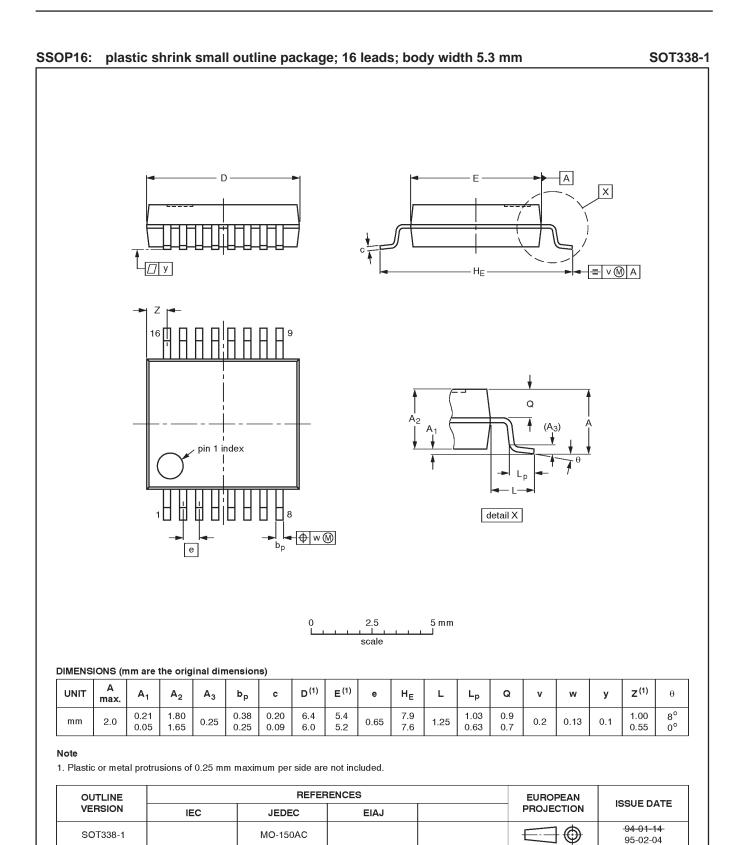
0.01

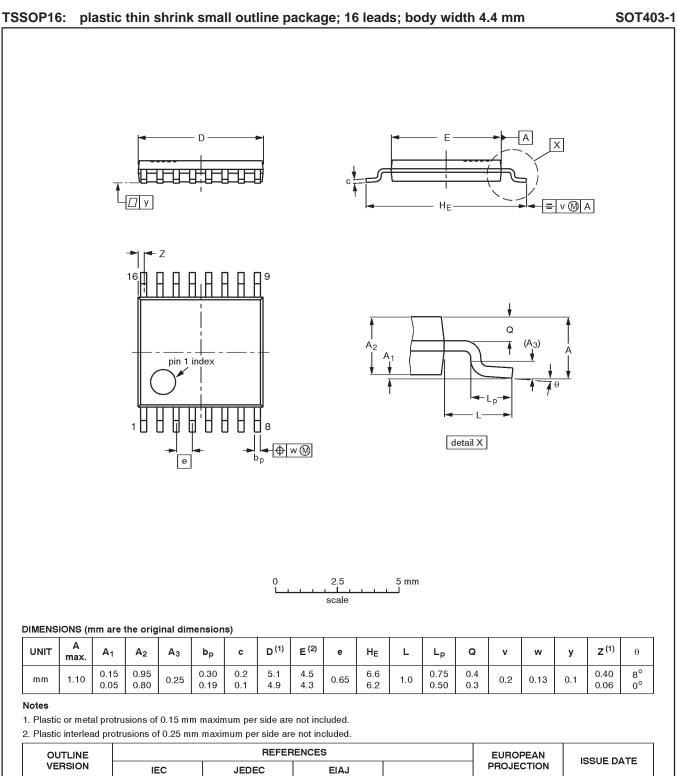
0.030

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Product specification







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Data sheet status

Data sheet status	Product status	Definition ^[1]
Objective specification	Development	This data sheet contains the design target or goal specifications for product development. Specification may change in any manner without notice.
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